

<b>Notice of References Cited</b>	Application/Control No. 10/065,920	Applicant(s)/Patent Under Reexamination VOLLERTSEN, ROLF-P.	
	Examiner Anjan K Deb	Art Unit 2858	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
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	C	US-			
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**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

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	U	Satake, H.; Toriumi, A.; (Dielectric breakdown mechanism of thin-SiO <sub>2</sub> studied by the post-breakdown resistance statistics. Electron Devices, IEEE Transactions on, Volume: 47, Issue: 4, April 2000 Pages: 741 - 745).
	V	Takeda, K.-I.; Hinode, K.; Oodake, I.; Oohashi, N.; Yamaguchi, H.; (Enhanced dielectric breakdown lifetime of the copper/silicon nitride/silicon dioxide structure. Reliability Physics Symposium Proceedings, 1998. 36th Annual. IEEE 98CH36173, pages 36-41.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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